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[\[NanoTech\]\[Memory\] Taiwan Innovates Globally Smallest 9nm Functional Resistive Memory with Lowest Programming-current](#)

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RTI (2010/12/14), udn.com, &The Liberty Times (2010/12/15) National Nano Device Laboratories (NDL), Taiwan, innovates the globally first smallest 9nm functional resistive memory cell with the lowest programming-current (